IN I EDINATIONAL SEADON HEPORT



A. CLASSIFICATION OF SUBJECT MATTER IPC 7 H01L29/786 H01L21/336

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols) IPC $7 \quad H01L$

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the International search (name of data base and, where practical, search terms used)

EPO-Internal

Category °	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
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Υ	EP 0 609 867 A (SEMICONDUCTOR ENERGY LAB) 10 August 1994 (1994-08-10) column 5, line 44 - line 47; claims 1,3 column 6, line 55 -column 7, line 11	1-27

Y Further documents are listed in the continuation of box C.	χ Patent family members are listed in annex.
Special categories of cited documents: A' document defining the general state of the art which is not considered to be of particular relevance E' earlier document but published on or after the international filling date L' document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) O' document referring to an oral disclosure, use, exhibition or other means P' document published prior to the international filling date but later than the priority date claimed	 "T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art. "&" document member of the same patent family
Date of the actual completion of the international search	Date of mailing of the international search report
22 June 2004	01/07/2004
Name and mailing address of the ISA European Patent Office, P.B. 5818 Patentiaan 2 NL – 2280 HV Rijswijk Tel. (+31–70) 340–2040, Tx. 31 651 epo nl, Fax: (+31–70) 340–3016	Authorized officer Juh 1 , A

INTERNATIONAL SEARCH REPORT

International Application No

C.(Continue	ation) DOCUMENTS CONSIDERED TO BE RELEVANT	Per/EP2004/001107
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A	US 6 017 779 A (MIYASAKA MITSUTOSHI) 25 January 2000 (2000-01-25) column 22, line 9 - line 47	13
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